

Form PTO-1449	LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use Several Sheets if Necessary)	ATTY. DOCKET NO.	SERIAL NO.
		CR00-001	
		Kurt Eisenbeiser et al.	
		FILING DATE	GROUP

10600 U.S. PTO
09/584601
05/31/00

REFERENCE DESIGNATION								U.S. PATENT DOCUMENTS		
EXAMINER INITIAL	DOCUMENT NUMBER	ISSUE DATE	NAME	CLASS	SUBCLASS	FILING DATE				
	AA									
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OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)	
SW	AO "Formation of SiEpi./MgO-Al ₂ O ₃ Epi./SiO ₂ /Si and Its Epitaxial Film Quality," Masao Mikami et al., Extended Abstracts of the 15 th Conference on Solid State Devices and Materials, Tokyo, 1983, pp. 31-34.
	AP
	AQ
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	AS

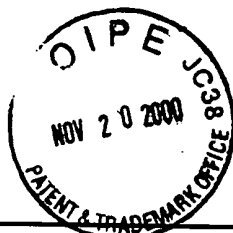
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EXAMINER INITIAL		DOCUMENT NUMBER	ISSUE DATE	NAME	CLAS S	SUBCLASS	FILING DATE
SNW	AA	5 2 2 5 0 3 1	7/6/93	McKee et al.	156	612	4/10/91
SNW	AB	5 4 5 0 8 1 2	9/19/95	McKee et al.	117	84	12/8/93
SNW	AC	5 4 8 2 0 0 3	1/9/96	McKee et al.	117	108	7/6/93
SNW	AD	5 8 3 0 2 7 0	11/3/98	McKee et al.	117	106	8/5/96
SNW	AE	5 5 1 4 4 8 4	5/7/96	Nashimoto	428	700	10/19/93
SNW	AF	5 3 9 3 3 5 2	2/28/95	Summerfelt	148	33.3	9/27/93

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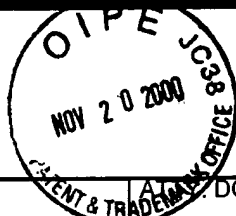
SNW	AO	"Crystalline Oxides on Silicon: The First Five Monolayers", R.A. McKee et al., Physical Review Letters, Vol. 81, No. 14, pp. 3014-3017.
SNW	AP	"Molecular Beam Epitaxy Growth of Epitaxial Barium Silicide, Barium Oxide, and Barium Titanate on Silicon", R.A. McKee et al., Oak Ridge National Laboratory, 1991 American Institute of Physics, pp. 782-784.
SNW	AQ	"Molecular Beam Epitaxy of SrTiO ₃ Films on Si(100)-2x1 with SrO Buffer Layer", Toyokazu Tambo et al., Jpn. J. Appl. Phys., Vol. 37 (1998) pp. 4454-4459.
SNW	AR	"Roles of Buffer Layers in Epitaxial Growth of SrTiO ₃ Films on Silicon Substrates", Bum Ki Moon et al., Jpn. J. Appl. Phys., Vol. 33 (1994) pp. 1472-1477.
SNW	AS	"The MBE Growth and Optical Quality of BaTiO ₃ and SrTiO ₃ Thin Films on MgO", R.A. McKee et al., Mat. Res. Soc. Symp. Proc. Vol. 341, pp. 309-314.
SNW	AT	"BaSi ₂ and Thin Film Alkaline Earth Silicides on Silicon", R.A. McKee et al., Appl. Phys. Lett. 63 (20), 15 November 1993, pp. 2818-2820.
SNW	AU	"Surface Structures and the Orthorhombic Transformation of Thin Film BaSi ₂ on Silicon", R. A. McKee et al., Mat. Res. Soc. Symp. Proc., Vol. 221., pp. 131-136.
SNW	AV	"Epitaxial Growth of SrTiO ₃ Films on Si(100) Substrates Using a Focused Electron Beam Evaporation Method", Hiroyuki Mori et al., Jpn. J. Appl. Phys., Vol. 30 (1991), pp.1415-1417.

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<i>SMW</i>	AA	5 2 2 5 0 3 1	7-6-93	McKee et al.			4-10-91
<i>SMW</i>	AB	5 4 8 2 0 0 3	1-9-96	McKee et al.			7-6-93
<i>SMW</i>	AC	5 7 6 7 5 4 3	6-16-98	Ooms et al.			9-16-96
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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO
<i>SMW</i>	AM	9 3 1 5 8 9 7	12-9-97	Patent Abstracts of Japan			X
<i>SMW</i>	AN	4 1 2 0 2 5 8	12-24-92	Germany			X
	AO						
	AP						
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OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

<i>SMW</i>	AS	"Molecular Beam Epitaxy of SrTiO ₃ Films on Si(100)-2 x 1 with SrO Buffer Layer", Toyokazu Tambo et al., Japanese Journal of Applied Physics, vol. 37, no. 1, pp. 4454-59.
<i>SMW</i>	AT	"Roles of buffer Layers in Epitaxial Growth of SrTiO ₃ Films on silicon Substrates", Bum Ki Moon et al., Japanese Journal of Applied Physics, vol. 33, pp. 1472-1477.
	AU	
	AV	
	AW	

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		C1200-001	69/584601
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	AB						
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OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)		
SPW	AW	"Growth of Crystalline SrTiO ₃ Films on Si Substrates Using Thin Fluoride Buffer Layers and Their Electrical Properties", Bum Ki Moon et al., Jpn. J. Appl. Phys., Vol. 33 (1994), pp. 5911-5916.
SPW	AX	"Heteroepitaxy of Dissimilar Materials", Materials Research Society Symposium Proceedings, Vol. 221, pp. 29-34.
SPW	AY	"Heteroepitaxy on Silicon: Fundamentals, Structure, and Devices", Materials Research Society Symposium Proceedings, Vol. 116, pp. 369-374.
SPW	AZ	"A Preliminary Consideration of the Growth Behaviour of CeO ₂ , SrTiO ₃ and SrVO ₃ films on Si Substrate", Hirotoishi Nagata, Thin Solid Films, 224(1993), pp. 1-3
SPW	BB	"Heteroepitaxial Growth of CeO ₂ (001) Films on Si(001) Substrates by Pulsed Laser Deposition in Ultrahigh Vacuum", Hirotoishi Nagata et al., Jpn. J. Appl. Phys., Vol. 30 (1991), pp. 1136-1138.
SPW	BC	"Heteroepitaxial Growth of SrO films on Si Substrates", Yuichi Kado et al., J. Appl. Phys. 61(6), 1987, pp.2398-2400.
SPW	BD	"Silicon Molecular Beam Epitaxy", Materials Research Society Symposium Proceedings, Vol. 220, pp. 595-600.
SPW	BE	"Effects of Buffer Layers in Epitaxial Growth of SrTiO ₃ Thin Film on Si(100)", Osamu Nkagawara et al., J. Appl. Phys. (1995), pp. 7226-7230.
SPW	BF	"A Proposal of Epitaxial Oxide Thin Film Structures for Future Oxide Electronics", M. Suzuki et al., Materials Science and Engineering B41 (1996), pp. 166-173.

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		JG00001	09/584601
		Eisenbeiser et al.	
		FILING DATE	GROUP
		April 10, 2001	

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U.S. PATENT DOCUMENTS

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<i>SNW</i>	A	4 5 2 3 2 1 1	6/11/85	Morimoto et al.	357	4	3/8/83
	B	5 4 7 8 6 5 3	12/26/96	Guenzer	428	446	4/4/94
	AA	3 8 0 2 9 6 7	4/9/74	Landany et al.	148	171	8/27/91
	AB	4 4 0 4 2 6 5	9/13/83	Manasevit	428	689	4/7/78
	AC	4 4 8 2 9 0 6	11/13/84	Hovel et al.	357	16	6/30/82
	AD	4 8 4 6 9 2 6	7/11/89	Kay et al.	156	612	9/3/87
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	AF	4 8 9 1 0 9 1	1/2/90	Shastry	156	606	6/8/87
	AG	4 9 2 8 1 5 4	5/22/90	Umeno et al.	357	16	3/20/89
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	AI	4 9 9 9 8 4 2	3/12/91	Huang et al.	372	45	3/1/89
	AJ	5 1 4 1 8 9 4	8/25/92	Bisaro et al.	437	132	7/20/90
	AK	5 1 5 5 6 5 8	10/13/92	Inam et al.	361	321	3/5/92
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	AT	5 5 5 6 4 6 3	9/17/96	Guenzer	117	90	6/5/95
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	AZ	5 8 0 1 1 0 5	9/1/98	Yano et al.	438	785	6/14/96
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	BC	5 8 7 4 8 6 0	2/23/99	Brunel et al.	330	285	12/4/96
	BD	6 0 0 2 3 7 5	12/14/99	Corman et al.	343	853	9/2/97
	BE	6 0 4 5 6 2 6	4/4/00	Yano et al.	148	33.4	6/23/98
	BF	6 0 5 5 1 7 9	4/25/00	Koganei et al.	365	158	5/17/99
	BG	6 0 6 4 0 7 8	5/16/00	Northrup et al.	257	96	5/22/98
	BH	6 1 0 3 0 0 8	8/15/00	McKee et al.	117	2	7/30/98
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	BJ	6 1 1 3 6 9 0	9/5/00	Yu et al.	117	84	6/8/98
<i>SNW</i>	BK	6 1 4 3 0 7 2	11/7/00	McKee et al.	117	08	4/6/99

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<i>Smw</i>	CN	"Integration of GaAs on Si using a spinel buffer layer, IBM Technical Bulletin," vol. 30, no. 6, Nov. 1987, p. 365
<i>Smw</i>	CM	"GaInAs Superconducting FET," IBM Technical Bulletin, vol. 36, no. 8, Aug. 1993, p. 655.
<i>Smw</i>	CO	"Epitaxial 3d Structure Using Mixed Spinel," IBM Technical Bulletin, vol. 30, no. 3, Aug. 1987, p. 1271.
<i>Smw</i>	CQ	"GaAs Heteroepitaxial Growth on Si Substrates with Thin Si Interlayers in Situ Annealed at High Temperatures," Yodo et al., 8257b Journal of Vacuum Science & Technology, 1995, no. 3, pp. 1000-1005.

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Smw R. W. K.

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<i>Smw</i>	DI	"Optimizing GMR Spin Valves: The Outlook for Improved Properties", W. F. Enghoff et al., 1998 Int'l NonVolatile Memory Technology Conference, pp. 34-37.
<i>Smw</i>	DJ	"Processing and Performance of Piezoelectric Films", Y. Wang et al., Univ. of MD, Wilcoxon Research Co., and Motorola Labs.
<i>Smw</i>	DK	"Nonlinear acoustoelectric interactions in GaAs/LiNbO ₃ structures", M. Rotter et al., 1999 American Institute of Physics, pp. 965-967.
<i>Smw</i>	DL	"Surface acoustic wave propagation on lead zirconate titanate thin films", K. Sreenivas et al., App. Phys. Lett. 52(9), 29 February 1988, pp. 709-711.
<i>Smw</i>	DM	"Single Chip fused hybrids for acousto-electric and acousto-optic applications", M. Rotter et al., 1997 American Institute of Physics, pp. 2097-2099.
<i>Smw</i>	DN	"Surface Acoustic Wave Propagation in PZT/YBCO/SrTiO ₃ and PbTiO ₃ /YBCO/SrTiO ₃ Epitaxial Heterostructures", Dept. of Physics & Astrophysics, Univ. of Delhi, pp. 275-283.
<i>Smw</i>	DO	"Ferroelectric Field Effect Transistor Based on Epitaxial Perovskite Heterostructures", S. Mathews et al., American Association for the Advancement of Science, 1997, pp.238-240.
<i>Smw</i>	DP	"Formation of Si Epi./MgO-Al ₂ O ₃ Epi./SiO ₂ /Si and Its Epitaxial Film Quality," Masao Mikami et al., Fundamental Research Laboratories and Microelectronics Laboratories, pp. 31-34.
<i>Smw</i>	DQ	"An Epitaxial Si/Insulator/Si Structure Prepared by Vacuum Deposition of CaF ₂ and Silicon," T. Asano et al., Graduate School of Science and Engineering, Tokyo Institute of Technology, pp. 143-151.
<i>Smw</i>	DR	"Reaction and Regrowth Control of CeO ₂ on Si(111) Surface for the Silicon-On-Insulator Structure," T. Chikyow et al., Appl. Phys. Lett. 65(8), 22 August 1994, pp. 1030-1032.
<i>Smw</i>	DS	"Epitaxial Growth of CeO ₂ (100) Films on Si(100) Substrates by Dual Ion Beams Reactive Sputtering," J.F. Kang et al., Solid State Communications, Vol. 108, No. 4, pp. 225-227.
<i>Smw</i>	DT	"Vertical-Cavity Surface-Emitting Lasers Come of Age," Robert A. Morgan et al., SPIE, Vol. 2683, pp. 18-29.
<i>Smw</i>	DU	"Technical Analysis of Qualcomm QCP-800 Portable Cellular Phone(Transmitter Circuitry)," Talus Corporation, Qualcomm QCP-800 Technical Analysis Report, December 10, 1996, pp. 5-8.
<i>Smw</i>	DV	"Properties of GaAs Si Grown by Molecular Beam Epitaxy," R. Houdre et al., Solid State and Molecular Sciences, 1990, pp. 91-114.
<i>Smw</i>	DW	"Gallium Arsenide and Other Compound Semiconductors on Silicon," S.F. Fang et al., J. Appl. Phys. 68(7), 1 October 1990, pp. R31-R58.

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<i>Smw</i>	DX	"Impact of GaAs Buffer Thickness on electronic Quality of GaAs Grown on Graded Ge/GeSi/Si Substrates," Carlin et al., Appl. Phys. Letter, vol. 76, no. 14, April 2000, pp. 1884-1886.
<i>Smw</i>	DY	"Epitaxial Integration of III-V Materials and Devices with Si Using Graded GeSi Buffers," Ringel et al., 27 th International Symposium on Compound Semiconductors, Oct. 2000.
<i>Smw</i>	DZ	"Progress in Compound-Semiconductor-on-Silicon-Heteroepitaxy with Fluoride Buffer Layers," Zogg et al., J. Electrochem Soc., vol. 136, no. 3, March 1989, pp. 775-779.
<i>Smw</i>	EA	"Oxide Defined GaAs Vertical-Cavity Surface-Emitting Lasers on Si Substrates," Xiong et al., IEEE Photonics Tech Letters, vol. 12, no. 2, Feb 2000, pp. 110-112.
<i>Smw</i>	EB	"Investigation of PZT/LSCO/Pt/Aerogel Thin Film Composites for Uncooled Pyroelectric IR Detectors," Clem et al., Mat. Res. Soc. Symp. Vol. 541, pg. 661-666.
<i>Smw</i>	EC	"Bound-To-Quasi-Bound Quantum-Well Infrared Photodetectors," Gunapala et al., NASA Tech Brief, vol. 22, no. 9.
<i>Smw</i>	ED	"Monolithic InGaAs-on-silicon Short Wave Infrared Detector Arrays," Joshi et al., Int'l. Society for Optical Engineering, vol. 2999, pp. 211-224.
<i>Smw</i>	EE	"Nanostructure and Chemistry of a (100)Mg/(100)GaAs Interface," Bruley et al., Appl. Phys Lett. 65(5), Aug. 1994, pp.564-566.
<i>Smw</i>	EF	"Epitaxial MgO on Si(001) for Y-Ba-Cu-O Thin Film Growth by Pulsed Laser Deposition," Fork et al., Appl. Phys Lett 58(20), May 1991, pp. 2294-2296.
<i>Smw</i>	EG	"Dielectrics on Semiconductors," Himpsel et al., Materials Science and Engineering, B1(1988), pp. 9-13.
<i>Smw</i>	EH	"Epitaxial La 0.67 Sr 0.33 MnO ₃ Magnetic Tunnel Junctions," J. Appl. Phys. 81(8), Apr. 1997 pp. 5509-5511
<i>Smw</i>	EI	"Colossal Magnetoresistance Magnetic Tunnel Junctions Grown by Molecular-Beam Epitaxy," O'Donnell et al., Appl. Physics Letters, vol. 76, no. 14, Apr. 2000, pp. 1914-1916.

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